

Shyam Bharadwaj

List of Publications by Citations

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Version: 2024-04-24

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

14
papers

179
citations

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h-index

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g-index

14
ext. papers

230
ext. citations

3
avg, IF

3.01
L-index

#	Paper	IF	Citations
14	MBE-grown 232±70 nm deep-UV LEDs using monolayer thin binary GaN/AlN quantum heterostructures. <i>Applied Physics Letters</i> , 2017 , 110, 041108	3.4	85
13	GaN/AlN quantum-disk nanorod 280 nm deep ultraviolet light emitting diodes by molecular beam epitaxy. <i>Optics Letters</i> , 2020 , 45, 121	3	21
12	Inactivation of <i>Listeria</i> and <i>E. coli</i> by Deep-UV LED: effect of substrate conditions on inactivation kinetics. <i>Scientific Reports</i> , 2020 , 10, 3411	4.9	18
11	Polarization control in nitride quantum well light emitters enabled by bottom tunnel-junctions. <i>Journal of Applied Physics</i> , 2019 , 125, 203104	2.5	14
10	Enhanced injection efficiency and light output in bottom tunnel-junction light-emitting diodes. <i>Optics Express</i> , 2020 , 28, 4489-4500	3.3	12
9	Bandgap narrowing and Mott transition in Si-doped Al _{0.7} Ga _{0.3} N. <i>Applied Physics Letters</i> , 2019 , 114, 113501	3.4	6
8	Nitride LEDs and Lasers with Buried Tunnel Junctions. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 015018	2	5
7	Light-emitting diodes with AlN polarization-induced buried tunnel junctions: A second look. <i>Applied Physics Letters</i> , 2020 , 117, 061104	3.4	5
6	Blue (In,Ga)N light-emitting diodes with buried n + p + tunnel junctions by plasma-assisted molecular beam epitaxy. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 060914	1.4	3
5	Enhanced efficiency in bottom tunnel junction InGaN blue LEDs 2021 ,		3
4	Monolithically p-down nitride laser diodes and LEDs obtained by MBE using buried tunnel junction design 2020 ,		2
3	Bottom tunnel junction blue light-emitting field-effect transistors. <i>Applied Physics Letters</i> , 2020 , 117, 031107	3.4	2
2	Efficient InGaN p-Contacts for deep-UV Light Emitting Diodes 2019 ,		2
1	Dislocation and indium droplet related emission inhomogeneities in InGaN LEDs. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 495106	3	1